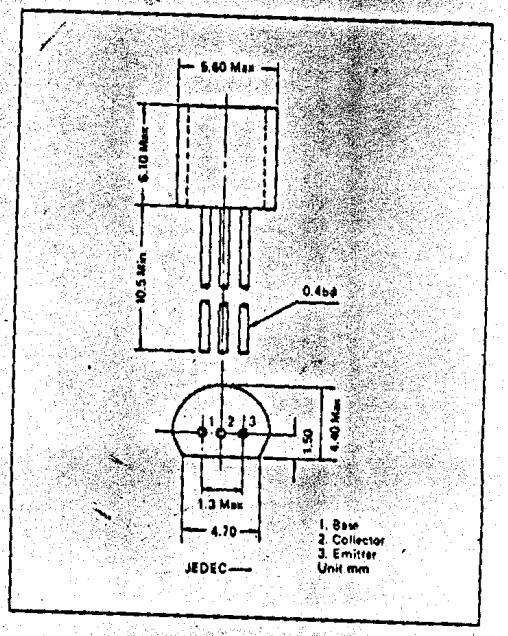
SONY

2SC1363, 1364

Silicon NPN APM Transistor

- 汎用増幅, 200mA, 320mW
- Complementary to 2SC1363: 2SA677
  2SC1364: 2SA678
- Family 2SC1633, 2SC1634



絶対最大定格 Absolute Maximum Ratings $T_a = 25°C$

Characteristics	Symbol	2SC1363	2SC1364
Collector-to-Base Voltage	V_{CBO}	25V	50V
Collector-to-Emitter Voltage	V_{CEO}	25V	50V
Emitter-to-Base Voltage	V_{EBO}	6V	
Collector Current	I_C	200 mA	
Base Current	I_B	50 mA	
Collector Power Dissipation	P_C	320 mW	
Junction Temperature	T_j	120°C	
Storage Temperature	T_{stg}	-30–+150°C	

電気的特性 Electrical Characteristics $T_a = 25°C$

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 25V$, $I_E = 0$			0.2	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6V$, $I_C = 0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE} = 3V$, $I_C = 1mA$	82		690	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50mA$, $I_B = 10mA$		0.10	0.30	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$			0.82	1.20	V
Small Signal Current Gain	$\|h_{fe}\|$	$V_{CE} = 6V$, $I_E = -2mA$, $f = 100MHz$		1.0	3.0	dB
Output Capacitance	C_{ob}	$V_{CB} = 6V$, $I_E = 0$, $f = 1MHz$		4.5	7.0	pF
Collector-to-Base Time Constant	$C_c \cdot r_{bb'}$	$V_{CB} = 6V$, $I_E = -2mA$, $f = 1.59MHz$		300	600	ps

規格細分 Classifications

Rank	h_{FE} ($I_C = 1mA$, $V_{CE} = 3V$)
5	82–175
6	129–276
7	204–442
7	326–609